

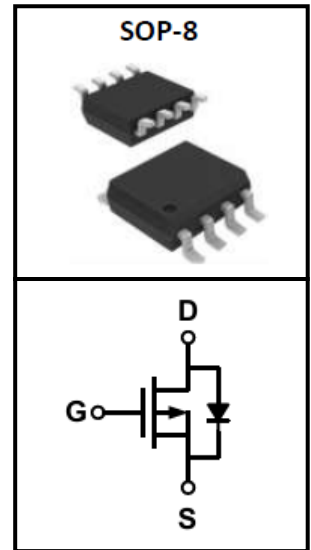
30V P-Channel Trench MOSFET

FEATURES

- Super Low Gate Charge
- 100% EAS Guaranteed
- RoHS compliant
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

APPLICATIONS

- Load switch
- Uninterruptible Power Supply (UPS)
- Pulse Width Modulation(PWM)



Device Marking and Package Information

| Device | Package | Marking |
|-----------|---------|-----------|
| CTS03P015 | SOP-8 | CTS03P015 |

Absolute Maximum Ratings at $T_J = 25^{\circ}\text{C}$ unless otherwise noted

| Parameter | Symbol | Value | Unit |
|---|----------------|----------|--------------------|
| Drain-Source Voltage ($V_{GS} = 0V$) | V_{DSS} | -30 | V |
| Drain Current-Continuous($T_C=25^{\circ}\text{C}$) (note1) | I_D | -12 | A |
| Drain Current-Continuous($T_C=100^{\circ}\text{C}$) (note1) | | -49 | |
| Gate Source Voltage | V_{GSS} | ± 20 | V |
| Single Pulse Avalanche Energy (note3) | E_{AS} | 125 | mJ |
| Power Dissipation $T_C = 25^{\circ}\text{C}$ (note4) | P_D | 1.5 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55~+175 | $^{\circ}\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|----------------------|
| Thermal Resistance, Junction-to-Ambient ($t \leq 10S$) (note1) | $R_{\theta JA}$ | 41 | $^{\circ}\text{C/W}$ |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified

| Parameter | Symbol | Test Conditions | Value | | | Unit |
|------------------------------------|---------------|--|-------|------|-----------|-----------|
| | | | Min. | Typ. | Max. | |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = -250\mu A$ | -30 | -- | -- | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -24V, V_{GS} = 0V, T_J = 25^{\circ}C$ | -- | -- | -1 | μA |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20V$ | -- | -- | ± 100 | nA |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\mu A$ | -1.0 | -1.6 | -3.0 | V |
| Drain-Source On-Resistance (note2) | $R_{DS(on)}$ | $V_{GS} = -10V, I_D = -10A$ | -- | -- | 15 | $m\Omega$ |
| | | $V_{GS} = -4.5V, I_D = -10A$ | -- | -- | 25 | $m\Omega$ |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0V,$ $V_{DS} = -15V,$ $f = 1.0MHz$ | -- | 2215 | -- | pF |
| Output Capacitance | C_{oss} | | -- | 310 | -- | |
| Reverse Transfer Capacitance | C_{rss} | | -- | 237 | -- | |
| Total Gate Charge (4.5V) | Q_g | $V_{DS} = -15V, I_D = -10A,$ $V_{GS} = -4.5V$ | -- | 20 | -- | nC |
| Gate-Source Charge | Q_{gs} | | -- | 5.1 | -- | |
| Gate-Drain Charge | Q_{gd} | | -- | 7.3 | -- | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DS} = -15V, R_L = 15\Omega$ $V_{GS} = -10V, R_G = 2.5\Omega$ $I_D = -1A$ | -- | 33.8 | -- | ns |
| Turn-on Rise Time | t_r | | -- | 35.6 | -- | |
| Turn-off Delay Time | $t_{d(off)}$ | | -- | 73 | -- | |
| Turn-off Fall Time | t_f | | -- | 11 | -- | |
| Body Diode Characteristics | | | | | | |
| Source-Drain Current(Body Diode) | I_{SD} | | -- | -- | -12 | A |
| Body Diode Voltage | V_{SD} | $T_J = 25^{\circ}C, I_{SD} = -1.7A, V_{GS} = 0V$ | -- | -- | -1.2 | V |

Notes

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH$
4. The power dissipation is limited by 175°C junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

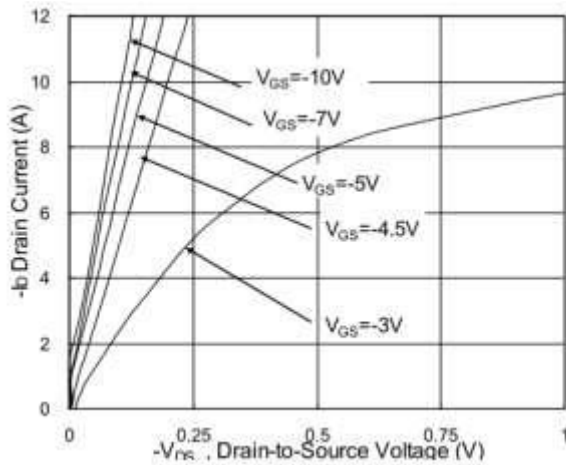


Fig.1 Typical Output Characteristics

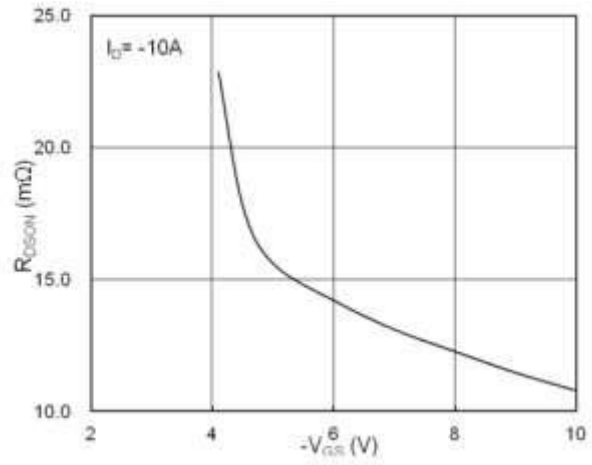


Fig.2 On-Resistance vs. G-S Voltage

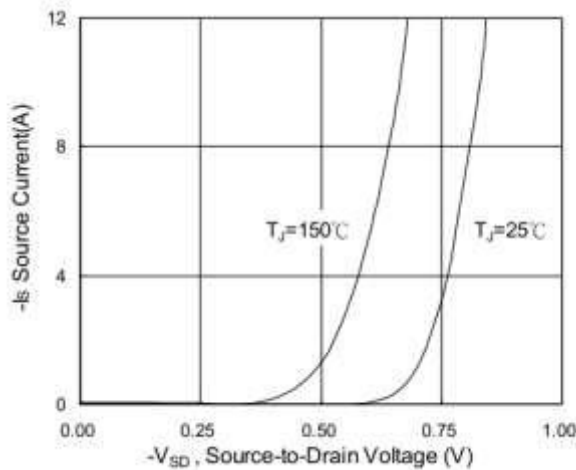


Fig.3 Forward Characteristics of Reverse

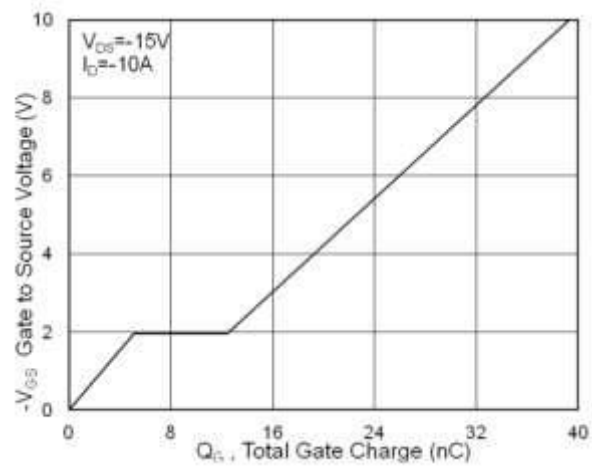


Fig.4 Gate-Charge Characteristics

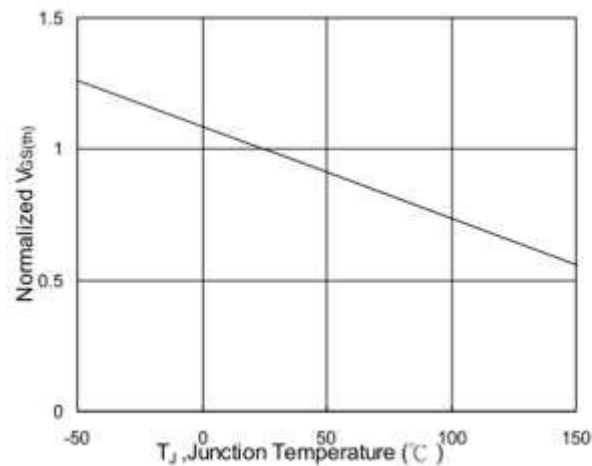


Fig.5 Normalized VGS(th) vs. TJ

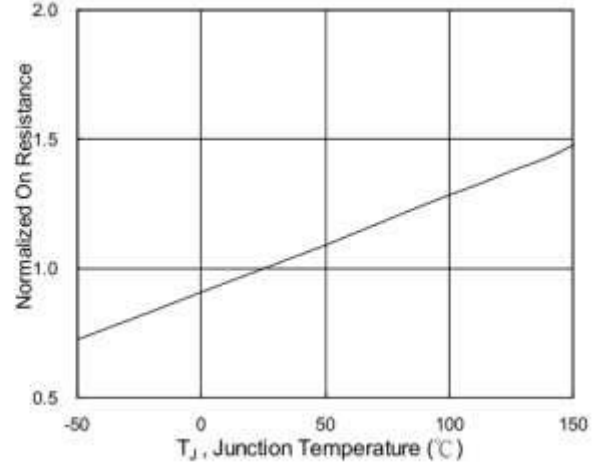


Fig.6 Normalized RDS(on) vs. TJ

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

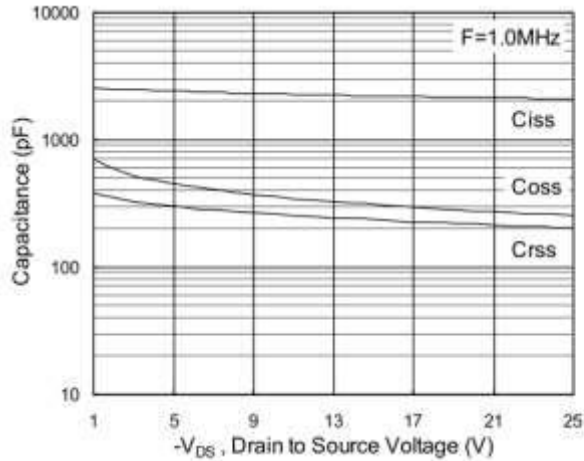


Fig.7 Capacitance

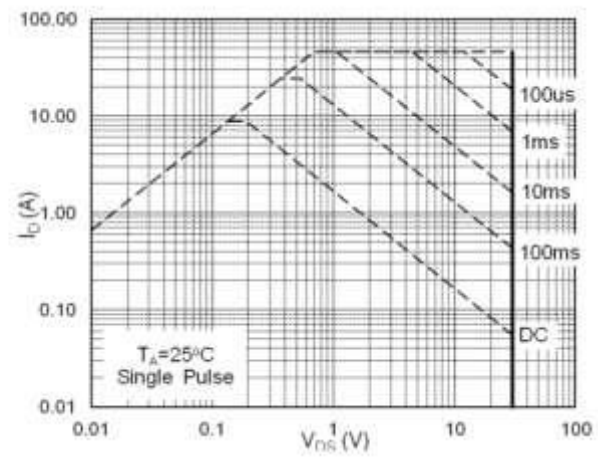


Fig.8 Safe Operating Area

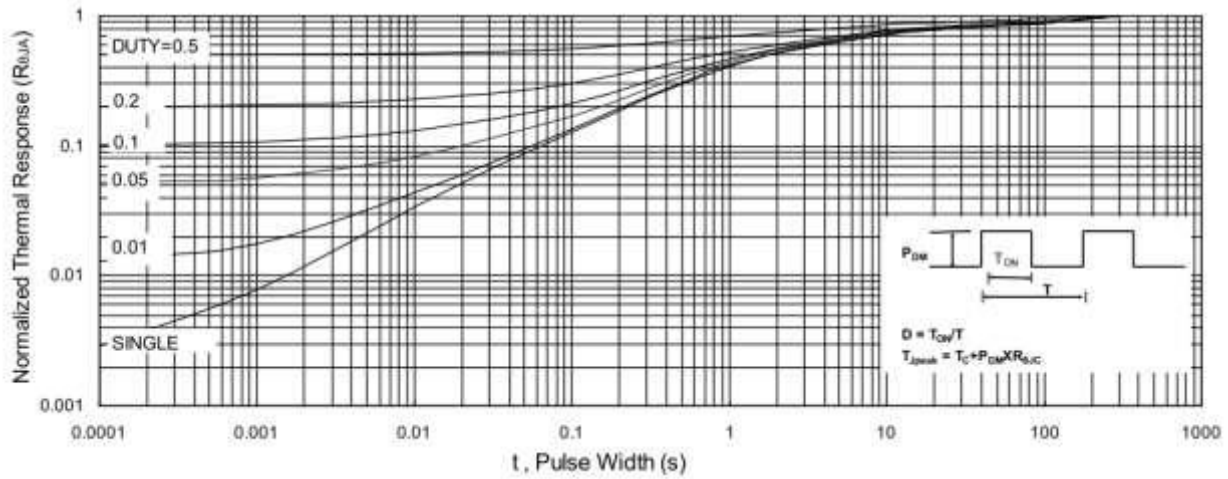
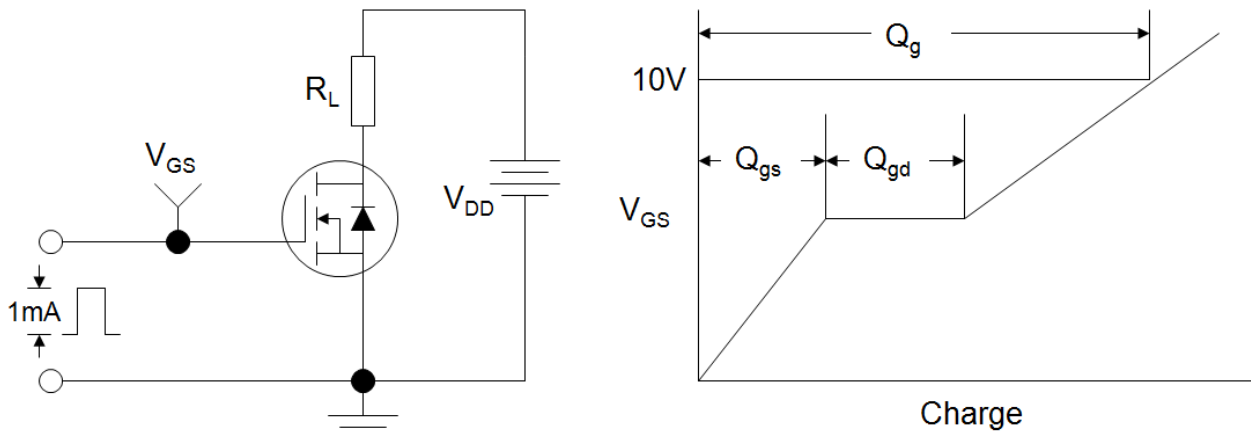
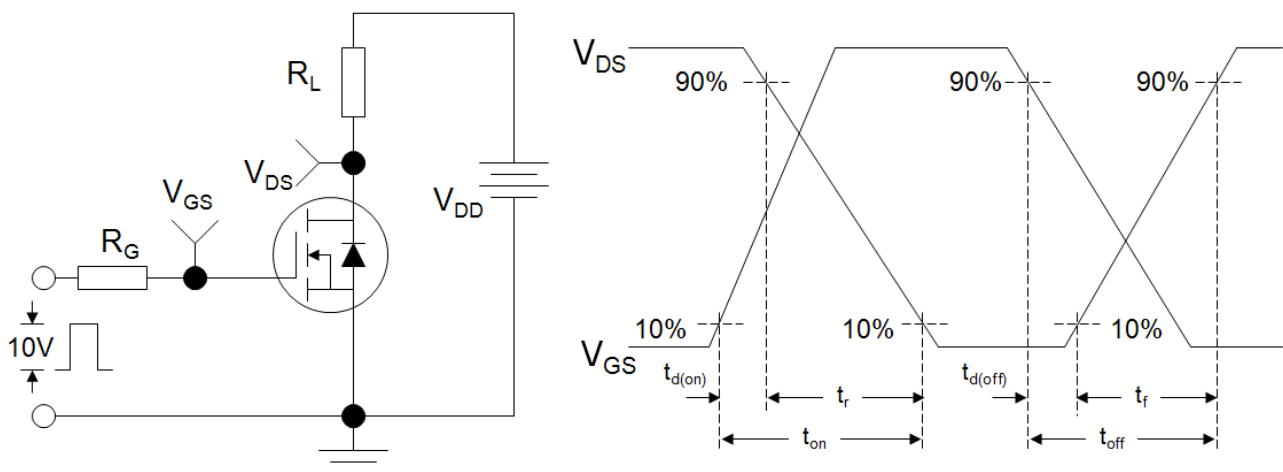
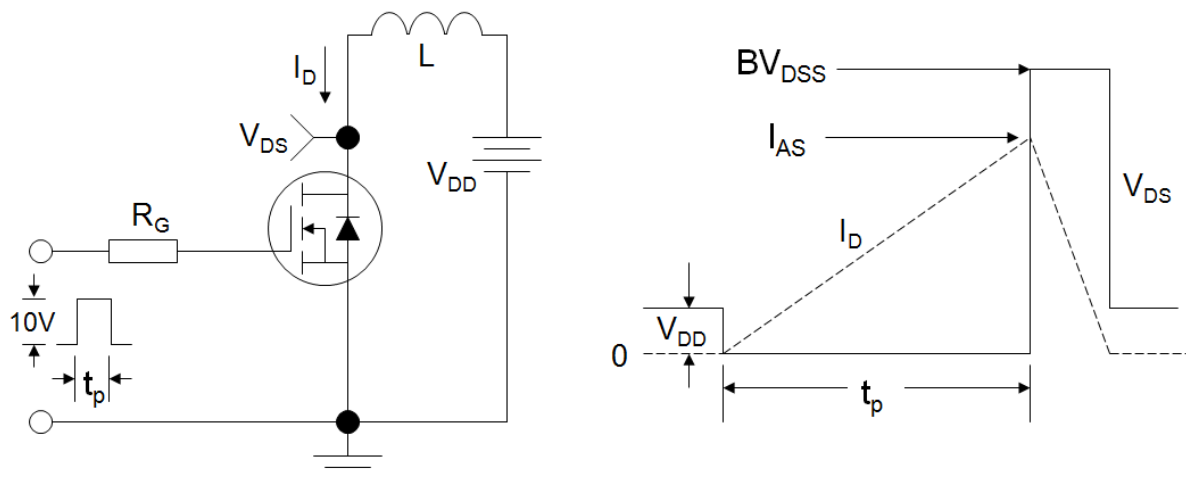
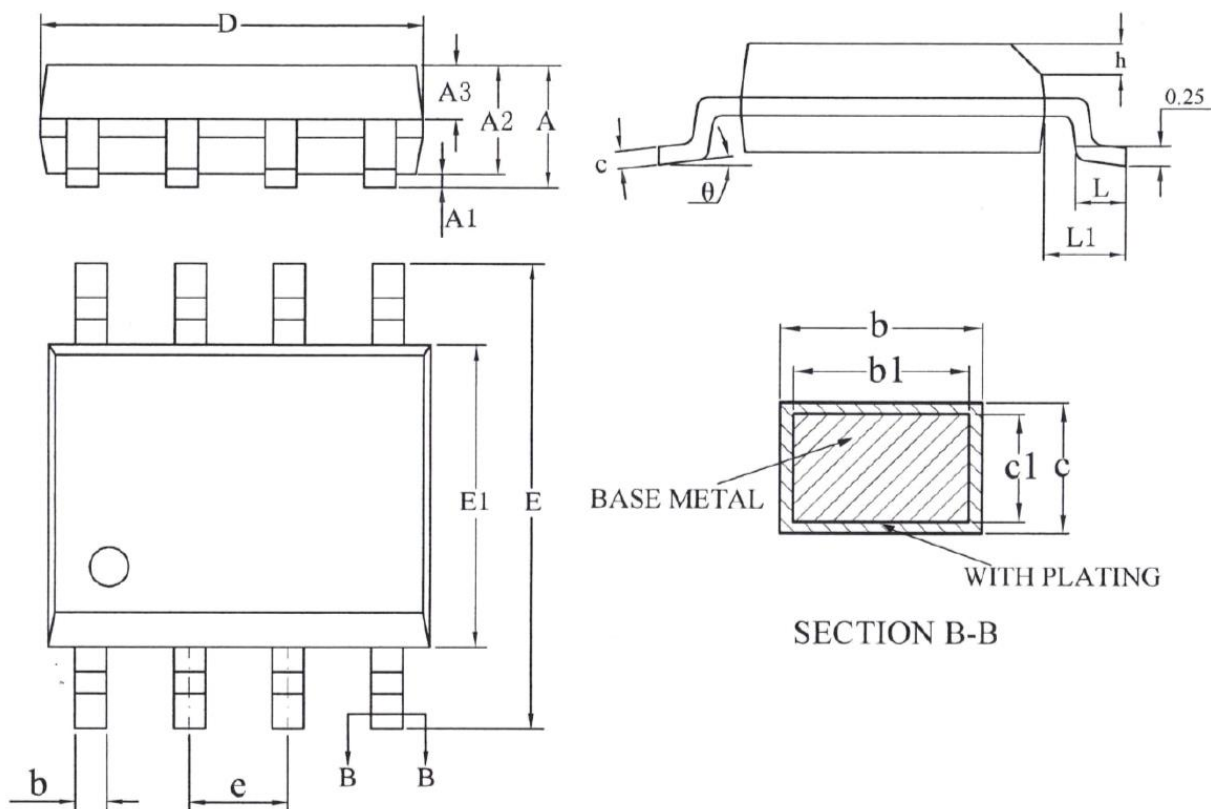


Fig.9 Normalized Maximum Transient Thermal Impedance

Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


SOP-8



| SYMBOL | MILLIMETER | | |
|--------|------------|------|-------|
| | MIN | NOM | MAX |
| A | — | — | 1.75 |
| A1 | 0.10 | — | 0.225 |
| A2 | 1.30 | 1.40 | 1.50 |
| A3 | 0.60 | 0.65 | 0.70 |
| b | 0.39 | — | 0.48 |
| b1 | 0.38 | 0.41 | 0.43 |
| c | 0.21 | — | 0.26 |
| c1 | 0.19 | 0.20 | 0.21 |

| SYMBOL | MILLIMETER | | |
|--------|------------|------|------|
| | MIN | NOM | MAX |
| D | 4.70 | 4.90 | 5.10 |
| E | 5.80 | 6.00 | 6.20 |
| E1 | 3.70 | 3.90 | 4.10 |
| e | 1.27BSC | | |
| h | 0.25 | — | 0.50 |
| L | 0.50 | — | 0.80 |
| L1 | 1.05BSC | | |
| θ | 0 | — | 8° |

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